

NDT452P

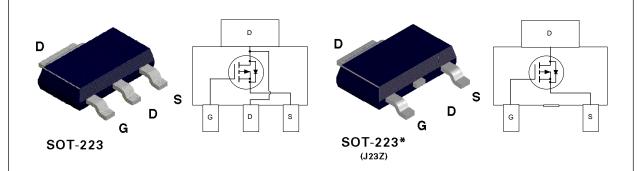
P-Channel Enhancement Mode Field Effect Transistor

General Description

Power SOT P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and DC motor control.

Features

- -3A, -30V. $R_{\text{DS(ON)}} = 0.18\Omega$ @ $V_{\text{GS}} = -10V$.
- High density cell design for extremely low R_{DS(ON)}.
- High power and current handling capability in a widely used surface mount package.



Absolute Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter		NDT452P	Units
V _{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I _D	Drain Current - Continuous	(Note 1a)	±3	А
	- Pulsed		±20	
P _D	Maximum Power Dissipation	(Note 1a)	3	W
		(Note 1b)	1.3	
		(Note 1c)	1.1	
T_J , T_{STG}	Operating and Storage Temperature Range		-65 to 150	°C
THERMA	AL CHARACTERISTICS			
R _{BJA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	42	°C/W
Rojc	Thermal Resistance, Junction-to-Case	(Note 1)	12	°C/W

^{*} Order option J23Z for cropped center drain lead.

Symbol	Parameter	Conditions	Min	Тур	Max	Units	
OFF CHA	RACTERISTICS			•			•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$				V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$				-2	μA
			T _J = 55°C			-25	μA
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	V _{GS} = -20 V, V _{DS} = 0 V				-100	nA
ON CHAR	ACTERISTICS (Note 2)	·					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-1	-2	-3	V
			T _J =125°C	-0.85	-1.7	-2.6	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, I_{D} = -3 \text{ A}$	•		0.15	0.18	Ω
			T _J =125°C		0.23	0.32	
		$V_{GS} = -4.5 \text{ V}, I_{D} = -2.2 \text{ A}$	$V_{GS} = -4.5 \text{ V}, I_D = -2.2 \text{ A}$				
I _{D(on)}	On-State Drain Current	$V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$	$V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$				Α
		$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-4.5				
g _{FS}	Forward Transconductance	$V_{DS} = -15 \text{ V}, I_{D} = -3 \text{ A}$		3.7		S	
DYNAMIC	CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, \ V_{GS} = 0 \text{ V},$		525		pF	
C _{oss}	Output Capacitance	f = 1.0 MHz			300		pF
C _{rss}	Reverse Transfer Capacitance				130		pF
SWITCHIN	NG CHARACTERISTICS (Note 2)						
$\mathbf{t}_{D(on)}$	Turn - On Delay Time	$V_{DD} = -10 \text{ V}, I_{D} = -1.0 \text{ A},$		8	40	ns	
t,	Turn - On Rise Time	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$	V_{GEN} = -10 V, R_{GEN} = 6 Ω			40	ns
$\mathbf{t}_{D(off)}$	Turn - Off Delay Time			25	90	ns	
t _r	Turn - Off Fall Time				8	50	ns
Q_g	Total Gate Charge	$V_{DS} = -10 \text{ V},$			15	25	nC
Q_{gs}	Gate-Source Charge	$I_D = -3 \text{ A}, \ V_{GS} = -10 \text{ V}$			1.6	4	nC
Q_{gd}	Gate-Drain Charge				4.5	8	nC

Electrical Characteristics (T _A = 25°C unless otherwise noted)									
Symbol	pol Parameter Conditions Min Typ Max Units								
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS									
I _s Maximum Continuous Drain-Source Diode Forward Current -2.5 A									
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \ I_{S} = -3 \text{ A} \ \text{(Note 2)}$			-1.2	V			

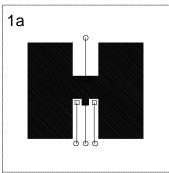
Notes:

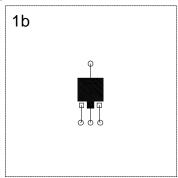
1. $R_{g,A}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{g,C}$ is guaranteed by design while $R_{g,C,A}$ is determined by the user's board design.

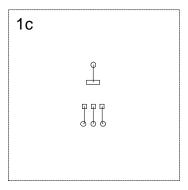
$$P_D(t) = \frac{T_J - T_A}{R_{\theta J} \dot{A}^{\dagger}} = \frac{T_J - T_A}{R_{\theta J} \dot{A}^{\dagger} R_{\theta C} \dot{A}^{\dagger}} = I_D^2(t) \times R_{DS(ON) \theta T_J}$$

Typical $R_{\theta_{JA}}$ using the board layouts shown below on 4.5"x5" FR-4 PCB in a still air environment:

- a. 42°C/W when mounted on a 1 in² pad of 2oz copper.
- b. 95°C/W when mounted on a 0.066 in $^{\!2}$ pad of 2oz copper.
- c. 110°C/W when mounted on a 0.0123 in² pad of 2oz copper.



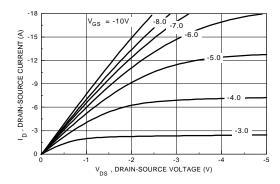




Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

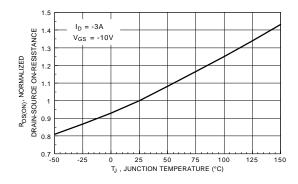
Typical Electrical Characteristics



3 V_{GS} = -4.0V V_{GS} = -4.5V V_{GS} = -4.5V

Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.



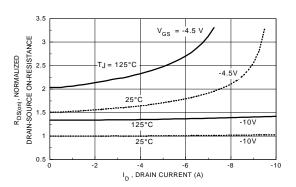
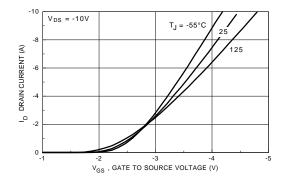


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Drain Current and Temperature.



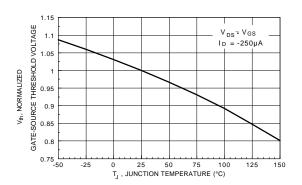
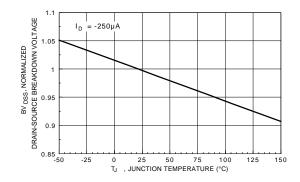


Figure 5. Transfer Characteristics.

Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics (continued)



TJ = 125°C

TJ = 125°C

TJ = 125°C

-55°C

-5°0

0.01

-0.4

-0.8

-1.2

-1.6

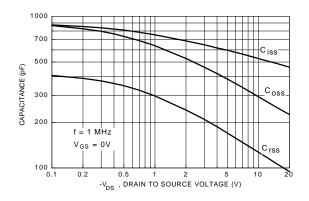
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V_{SD} , BODY DIODE FORWARD VOLTAGE (V)

Vgs = 0V

Figure 7. Breakdown Voltage Variation with Temperature.

Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.



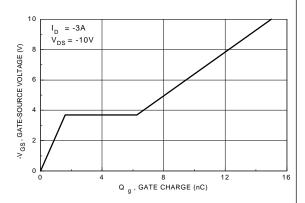
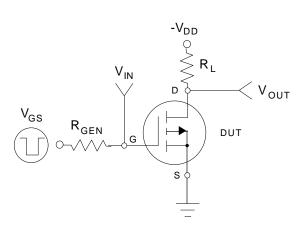


Figure 9. Capacitance Characteristics.

Figure 10. Gate Charge Characteristics.



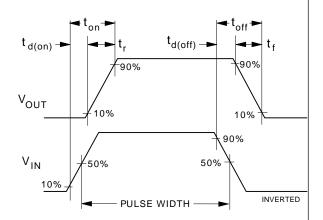
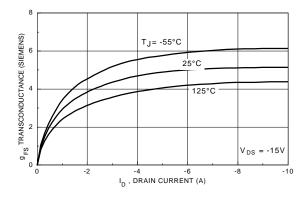


Figure 11. Switching Test Circuit.

Figure 12. Switching Waveforms.

Typical Electrical Characteristics (continued)



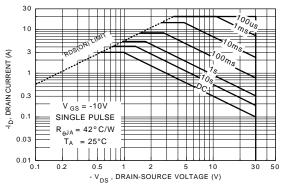


Figure 13. Transconductance Variation with Drain **Current and Temperature.**

Figure 14. Maximum Safe Operating Area.

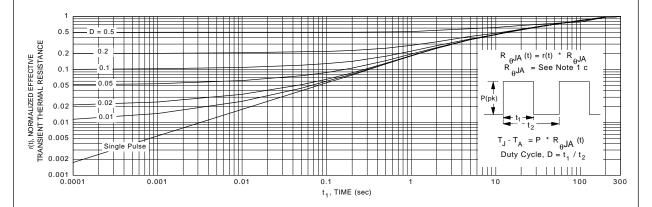


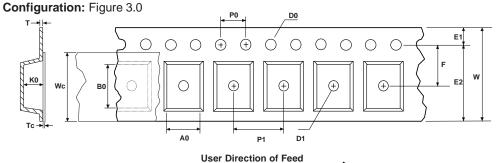
Figure 15. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c. Transient thermal response will change depending on the circuit board design.



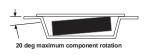


SOT-223 Embossed Carrier Tape

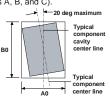


Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-223 (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



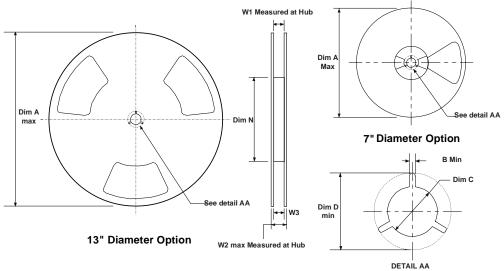
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

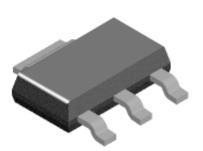
SOT-223 Reel Configuration: Figure 4.0

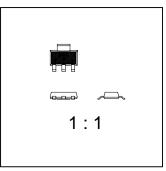


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

SOT-223 Tape and Reel Data and Package Dimensions, continued

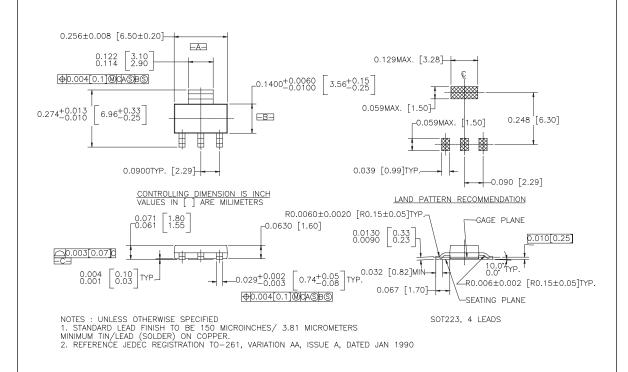
SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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